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**Christoph K. Hohle**  
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- 2 EUV Materials I: Metal-Based EUV Resists: Joint Session with Conferences 10146 and 10143  
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**Robert L. Brainard**, SUNY CNSE/SUNYIT (United States)
- 3 EUV Materials II: Fundamentals I: Joint Session with Conferences 10146 and 10143  
**Clifford L. Henderson**, Georgia Institute of Technology (United States)  
**Anna Lio**, Intel Corporation (United States)
- 4 Tutorial Session: Joint Session with Conferences 10143 and 10146  
**Eric M. Panning**, Intel Corporation (United States)  
**Kenneth A. Goldberg**, Lawrence Berkeley National Laboratory (United States)
- 5 EUV Materials III: Fundamentals II  
**Chao Fang**, KLA-Tencor Texas (United States)  
**Jim W. Thackeray**, Dow Electronic Materials (United States)
- 6 EUV Materials IV: Novel Materials and Processes  
**Jason K. Stowers**, Inpria Corporation (United States)  
**Ramakrishnan Ayothi**, JSR Micro, Inc. (United States)
- 7 Patterning Materials and Etch: Joint Session with Conferences 10146 and 10149  
**Qinghuang Lin**, IBM Thomas J. Watson Research Center (United States)  
**Sebastian U. Engelmann**, IBM Thomas J. Watson Research Center (United States)
- 8 3D Resist Effects and Modeling: Joint Session with Conferences 10146 and 10147  
**Carlos Fonseca**, Tokyo Electron America, Inc. (United States)  
**Rick Uchida**, Tokyo Ohka Kogyo America, Inc. (United States)
- 9 DSA Process and Integration: Joint Session with Conferences 10146 and 10144  
**Ralph R. Dammel**, EMD Performance Materials Corporation (United States)  
**Chi-Chun Liu**, IBM Corporation (United States)

- 10 DSA Materials and Processes: Joint Session with Conferences 10146 and 10144  
**Daniel P. Sanders**, IBM Research - Almaden (United States)  
**Benjamin M. Rathsack**, Tokyo Electron America, Inc. (United States)
- 11 DSA Novel Materials  
**Mark H. Somervell**, Tokyo Electron America, Inc. (United States)  
**Steve S. Putna**, Intel Corporation (United States)
- 12 DSA Modelling and Fundamentals  
**Raluca Tiron**, CEA-LETI (France)  
**Douglas J. Guerrero**, Brewer Science, Inc. (Belgium)
- 13 Hardmasks and Underlayer Materials  
**Ryan Callahan**, FUJIFILM Electronic Materials U.S.A., Inc. (United States)  
**Gilles R. Amblard**, SAMSUNG Austin Semiconductor LLC (United States)
- 14 Process Integration and Multipatterning  
**Scott W. Jessen**, Texas Instruments Inc. (United States)  
**Nobuyuki N. Matsuzawa**, Panasonic Corporation (Japan)

